

FDS4435A

P-Channel Logic Level PowerTrench® MOSFET

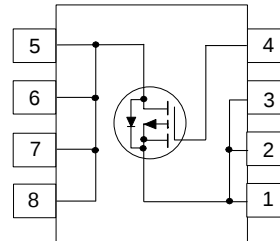
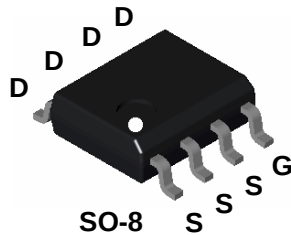
General Description

This P-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

These devices are well suited for notebook computer applications: load switching and power management, battery charging circuits, and DC/DC conversion.

Features

- -9 A, -30 V. $R_{DS(ON)} = 0.017 \Omega @ V_{GS} = -10 \text{ V}$
 $R_{DS(ON)} = 0.025 \Omega @ V_{GS} = -4.5 \text{ V}$
- Low gate charge (21nC typical).
- High performance trench technology for extremely low $R_{DS(ON)}$.
- High power and current handling capability.



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	-30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current - Continuous (Note 1a) - Pulsed	-9	A
		-50	
P_D	Power Dissipation for Single Operation (Note 1a) (Note 1b) (Note 1c)	2.5	W
		1.2	
		1	
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDS4435A	FDS4435A	13"	12mm	2500 units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, Referenced to 25°C		-26		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -24\text{ V}, V_{GS} = 0$ $T_J = 125^\circ\text{C}$			-1 -10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1	-1.7	-2	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, Referenced to 25°C		4.2		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -9\text{ A}$ $T_J = 125^\circ\text{C}$		0.015 0.021	0.017 0.030	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -7\text{ A}$		0.023	0.025	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = -10\text{ V}, V_{DS} = -5\text{ V}$	-40			A
g_{FS}	Forward Transconductance	$V_{DS} = -10\text{ V}, I_D = -9\text{ A}$		25		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}$ $f = 1.0\text{ MHz}$		2010		pF
C_{oss}	Output Capacitance			590		pF
C_{rss}	Reverse Transfer Capacitance			260		pF

Switching Characteristics (Note 2)

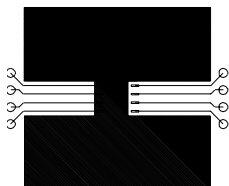
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -15\text{ V}, I_D = -1\text{ A}$ $V_{GS} = -10\text{ V}, R_{GEN} = 6\text{ }\Omega$		12	22	ns
t_r	Turn-On Rise Time			15	27	ns
$t_{d(off)}$	Turn-Off Delay Time			100	140	ns
t_f	Turn-Off Fall Time			55	80	ns
Q_g	Total Gate Charge	$V_{DS} = -15\text{ V}, I_D = -9\text{ A}$ $V_{GS} = -5\text{ V},$		21	30	nC
Q_{gs}	Gate-Source Charge			6		nC
Q_{gd}	Gate-Drain Charge			8		nC

Drain-Source Diode Characteristics and Maximum Ratings

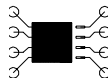
I _S	Maximum Continuous Drain-Source Diode Forward Current				-2.1	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -2.1 A (Note 2)		0.75	-1.2	V
t _{rr}	Source-Drain Reverse Recovery Time	I _F = -10 A, dI _F /dt = 100 A/μS		36	80	ns

Notes:

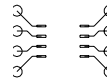
1: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50° C/W when mounted on a 1 in^2 pad of 2 oz. copper.



b) 105° C/W when mounted on a 0.04 in^2 pad of 2 oz. copper.



c) 125° C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2: Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

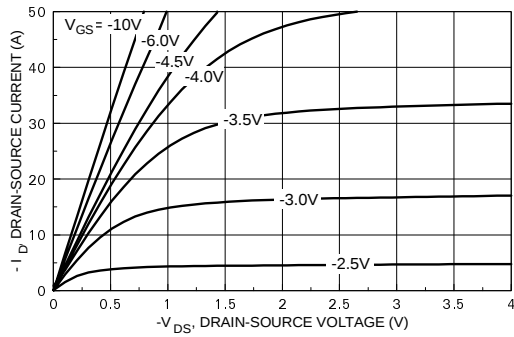


Figure 1. On-Region Characteristics

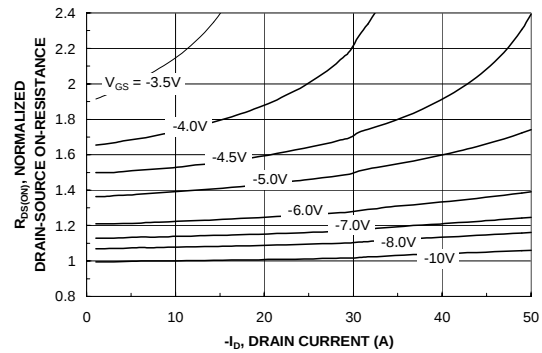


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

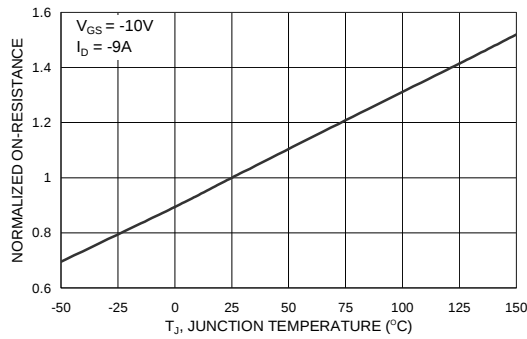


Figure 3. On-Resistance Variation with Temperature

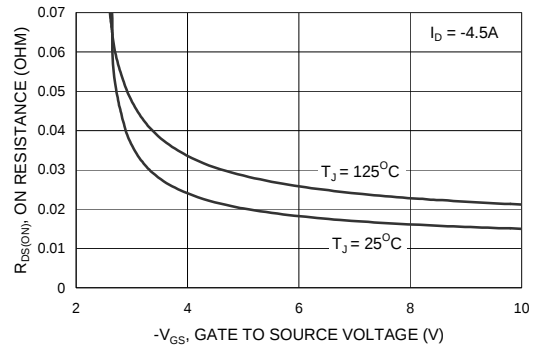


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

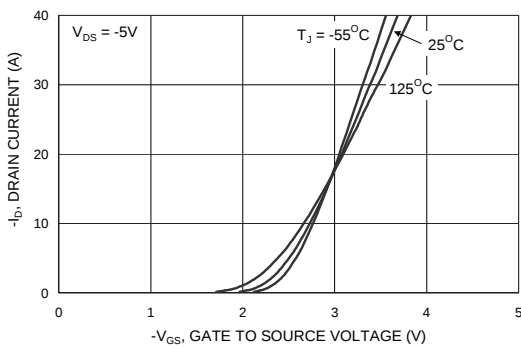


Figure 5. Transfer Characteristics

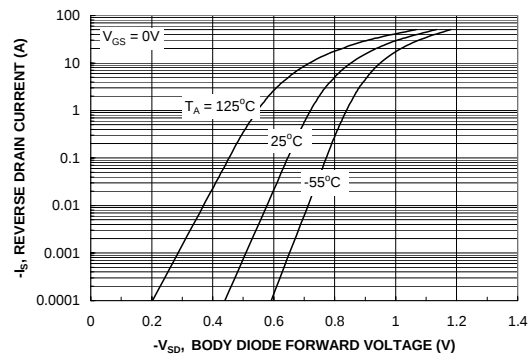


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Characteristics (continued)

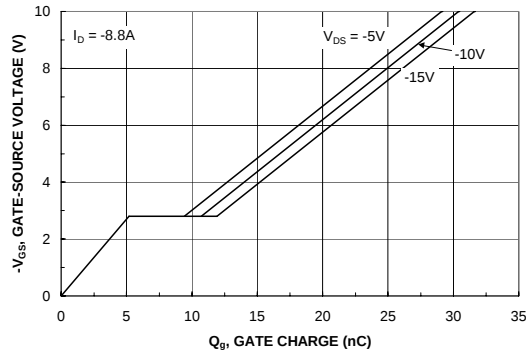


Figure 7. Gate-Charge Characteristics

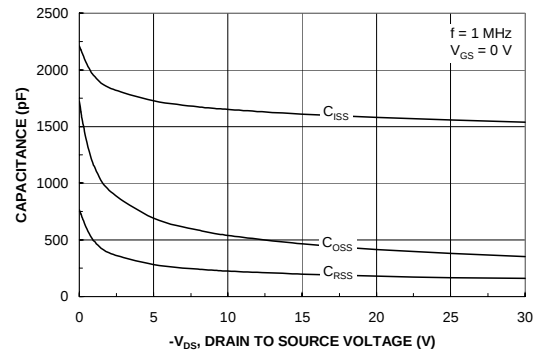


Figure 8. Capacitance Characteristics

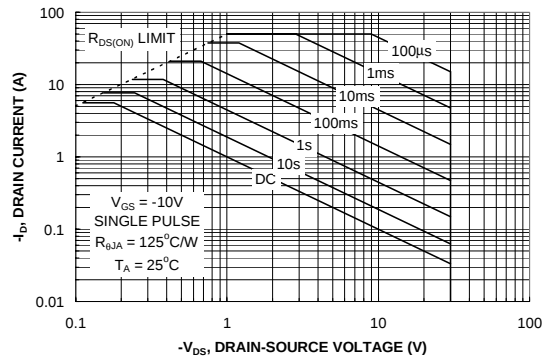


Figure 9. Maximum Safe Operating Area

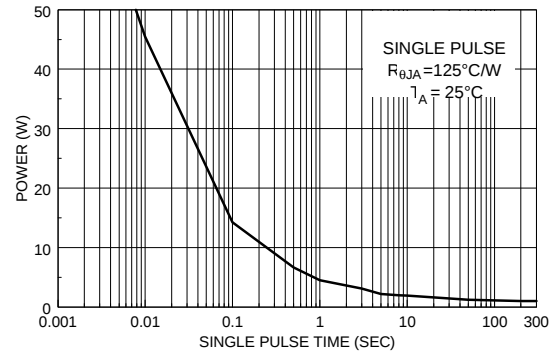


Figure 10. Single Pulse Maximum Power Dissipation

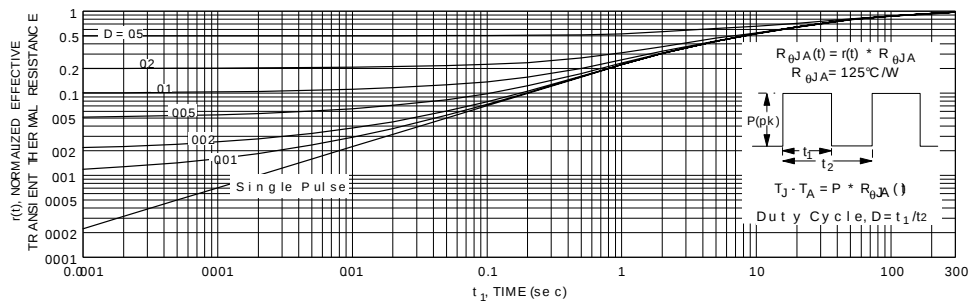


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

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Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.